Dual General Purpose Transistor

The NST857BDP6T5G device is a spin-off of our popular SOT-23/SOT-323/SOT-563 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-963 six-leaded surface mount package. By putting two discrete devices in one package, this device is ideal for low-power surface mount applications where board space is at a premium.

Features

- h_{FE}, 220-475
- Low $V_{CE(sat)}$, $\leq 0.3 \text{ V}$
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- This is a Pb-Free Device

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Collector - Emitter Voltage		V_{CEO}	-45	Vdc
Collector - Base Voltage		V _{CBO}	-50	Vdc
Emitter – Base Voltage		V _{EBO}	-6.0	Vdc
Collector Current - Continuous		Ic	-100	mAdc
Electrostatic Discharge	HBM MM	ESD Class	2 B	

THERMAL CHARACTERISTICS

Characteristic (Single Heated)	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C (Note 1)	P _D	240 1.9	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	520	°C/W
Total Device Dissipation T _A = 25°C Derate above 25°C (Note 2)	P _D	280 2.2	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	446	°C/W
Characteristic (Dual Heated) (Note 3)	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C (Note 1)	P _D	350 2.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	357	°C/W
Total Device Dissipation T _A = 25°C Derate above 25°C (Note 2)	P _D	420 3.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	297	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to	°C

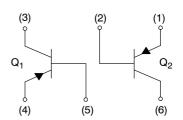
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. FR-4 @ 100 mm², 1 oz. copper traces, still air. 2. FR-4 @ 500 mm², 1 oz. copper traces, still air.
- 3. Dual heated values assume total power is sum of two equally powered channels.



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NST857BDP6T5G



SOT-963 CASE 527AD **PLASTIC**

MARKING DIAGRAM



K = Device Code

= Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

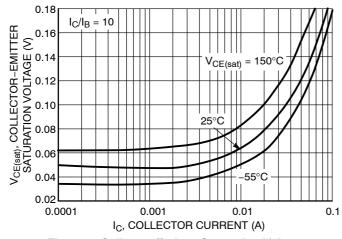
ORDERING INFORMATION

Device	Package	Shipping [†]
NST857BDP6T5G	SOT-963 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	·				
Collector - Emitter Breakdown Voltage (I _C = -10 mA)	V _{(BR)CEO}	-45	-	-	V
Collector – Emitter Breakdown Voltage ($I_C = -10 \mu A$, $V_{EB} = 0$)	V _{(BR)CES}	-50	-	-	V
Collector – Base Breakdown Voltage (I _C = -10 μA)	V _{(BR)CBO}	-50	-	-	V
Emitter – Base Breakdown Voltage (I _E = –1.0 μA)	V _{(BR)EBO}	-5.0	-	-	V
Collector Cutoff Current ($V_{CB} = -30 \text{ V}$) ($V_{CB} = -30 \text{ V}$, $T_A = 150^{\circ}\text{C}$)	I _{CBO}	- -	- -	-15 -4.0	nA μA
ON CHARACTERISTICS	·	•	•	•	•
DC Current Gain	h _{FE}	- 220	150 290	- 475	-
Collector – Emitter Saturation Voltage (I_C = -10 mA, I_B = -0.5 mA) (I_C = -100 mA, I_B = -5.0 mA)	V _{CE(sat)}	- -	- -	-0.3 -0.7	V
Base – Emitter Saturation Voltage (I_C = -10 mA, I_B = -0.5 mA) (I_C = -100 mA, I_B = -5.0 mA)	V _{BE(sat)}	- -	-0.7 -0.9	- -	V
Base – Emitter On Voltage (I_C = -2.0 mA, V_{CE} = -5.0 V) (I_C = -10 mA, V_{CE} = -5.0 V)	V _{BE(on)}	-0.6 -	- -	-0.75 -0.82	V
SMALL-SIGNAL CHARACTERISTICS				_	_
Current – Gain – Bandwidth Product (I _C = –10 mA, V _{CE} = –5.0 Vdc, f = 100 MHz)	f _T	100	_	-	MHz
Output Capacitance (V _{CB} = -10 V, f = 1.0 MHz)	C _{obo}	-	-	4.5	pF
Input Capacitance (V _{EB} = -0.5 V, f = 1.0 MHz)	C _{ibo}	_	_	10	pF
Noise Figure (I _C = -0.2 mA, V _{CE} = -5.0 Vdc, R _S = 2.0 k Ω , f = 1.0 kHz, BW = 200 Hz)	NF	-	-	10	dB





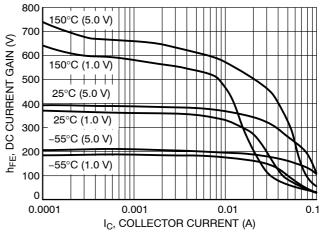


Figure 2. DC Current Gain vs. Collector Current

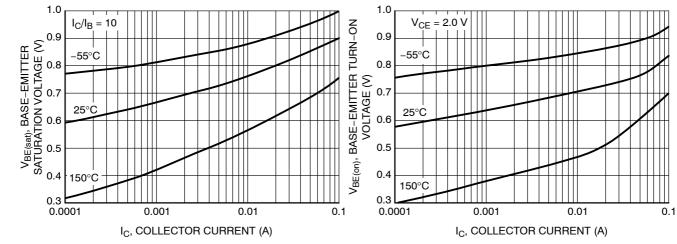


Figure 3. Base Emitter Saturation Voltage vs.
Collector Current

Figure 4. Base Emitter Turn-On Voltage vs.
Collector Current

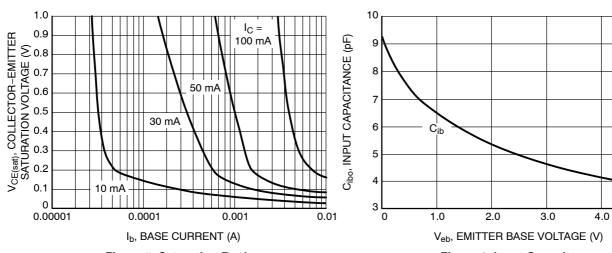


Figure 5. Saturation Region

Figure 6. Input Capacitance

5.0

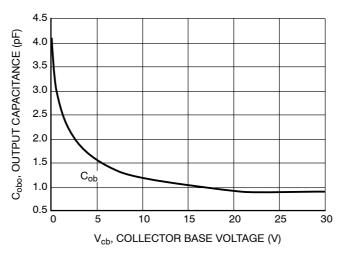
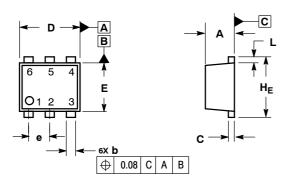


Figure 7. Output Capacitance

PACKAGE DIMENSIONS

SOT-963 CASE 527AD-01 ISSUE B

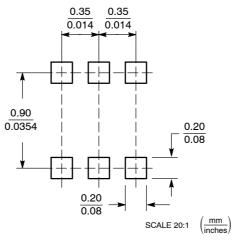


NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 V14 5M 1982
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.34	0.37	0.40			
b	0.10	0.15	0.20	0.004	0.006	0.008
С	0.07	0.12	0.17	0.003	0.005	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
E	0.75	0.80	0.85	0.03	0.032	0.034
е	0.35 BSC			0.014 BSC		
L	0.05	0.10	0.15	0.002	0.004	0.006
HE	0.95	1.00	1.05	0.037	0.039	0.041

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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